

THE RF MOSFET LINE RF POWER FIELD EFFECT TRANSISTOR

Manufacturers	NXP Semiconductor
Package/Case	TO-62
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for MRF372 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

MRF372 is a high-frequency NPN bipolar transistor designed for use in radio frequency (RF) power amplifiers in the 136-174 MHz range. It is manufactured by Motorola Solutions, Inc. (now part of NXP Semiconductors) and is available in a TO-272 package.

Features

High power gain: The transistor offers a typical power gain of 12 dB at 136 MHz and 10 dB at 174 MHz, making it suitable for high-frequency applications.

High power output: The MRF372 is capable of delivering up to 60 watts of power output at 136 MHz and up to 40 watts of power output at 174 MHz.

Broadband performance: The transistor offers a broadband frequency response, which makes it suitable for use in a wide range of applications.

High linearity: The MRF372 exhibits high linearity, which is essential for maintaining signal integrity and minimizing distortion.

Application

Two-way radios

Base stations

Repeaters

RF generators

Test equipment



Related Products



[MRF6S9125NR1](#)

NXP Semiconductor
TO-270



[MRF9030LR1](#)

NXP Semiconductor
NI-360-3



[MRF8P20160HSR3](#)

NXP Semiconductor
NI-780S-4



[MRF6V2300NBR1](#)

NXP Semiconductor
TO-272



[MRF6S20010GNR1](#)

NXP Semiconductor
TO-270



[MRF8P20100HSR3](#)

NXP Semiconductor
NI-780S-4



[MRF6VP2600HR6](#)

NXP Semiconductor
NI-1230



[MRF6VP2600H](#)

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